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(54) **SEMICONDUCTOR DEVICE WITH DEEP TRENCH ISOLATION AND TRENCH CAPACITOR**

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(57)

ABSTRACT

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Related U.S. Application Data

(62) Division of application No. 16/232,322, filed on Dec. 26, 2018, now Pat. No. 10,811,543.

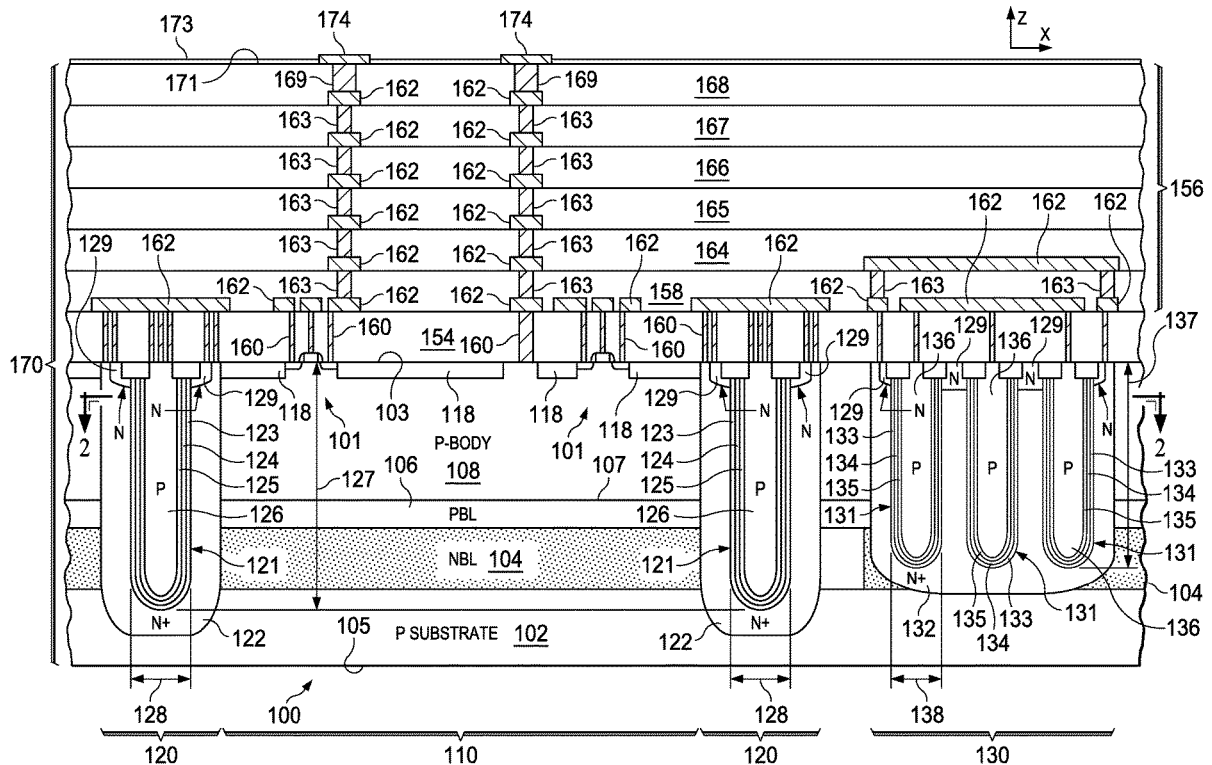
Publication Classification

(51) **Int. Cl.**

H01L 29/94 (2006.01)

H01L 29/08 (2006.01)

A semiconductor device with an isolation structure and a trench capacitor, each formed using a single resist mask for etching corresponding first and second trenches of different widths and different depths, with dielectric liners formed on the trench sidewalls and polysilicon filling the trenches and deep doped regions surrounding the trenches, including conductive features of a metallization structure that connect the polysilicon of the isolation structure trench to the deep doped region to form an isolation structure.



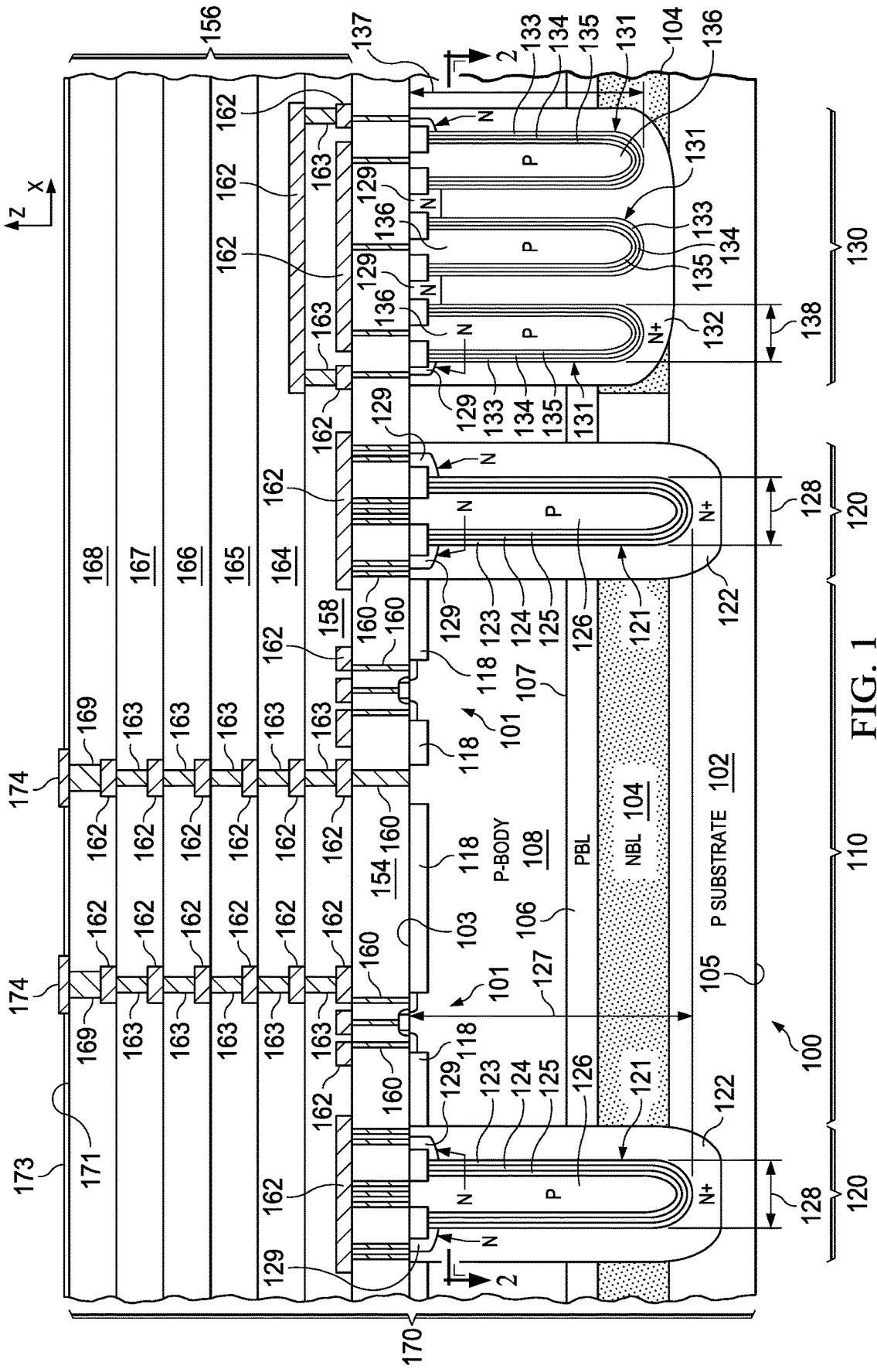


FIG. 1

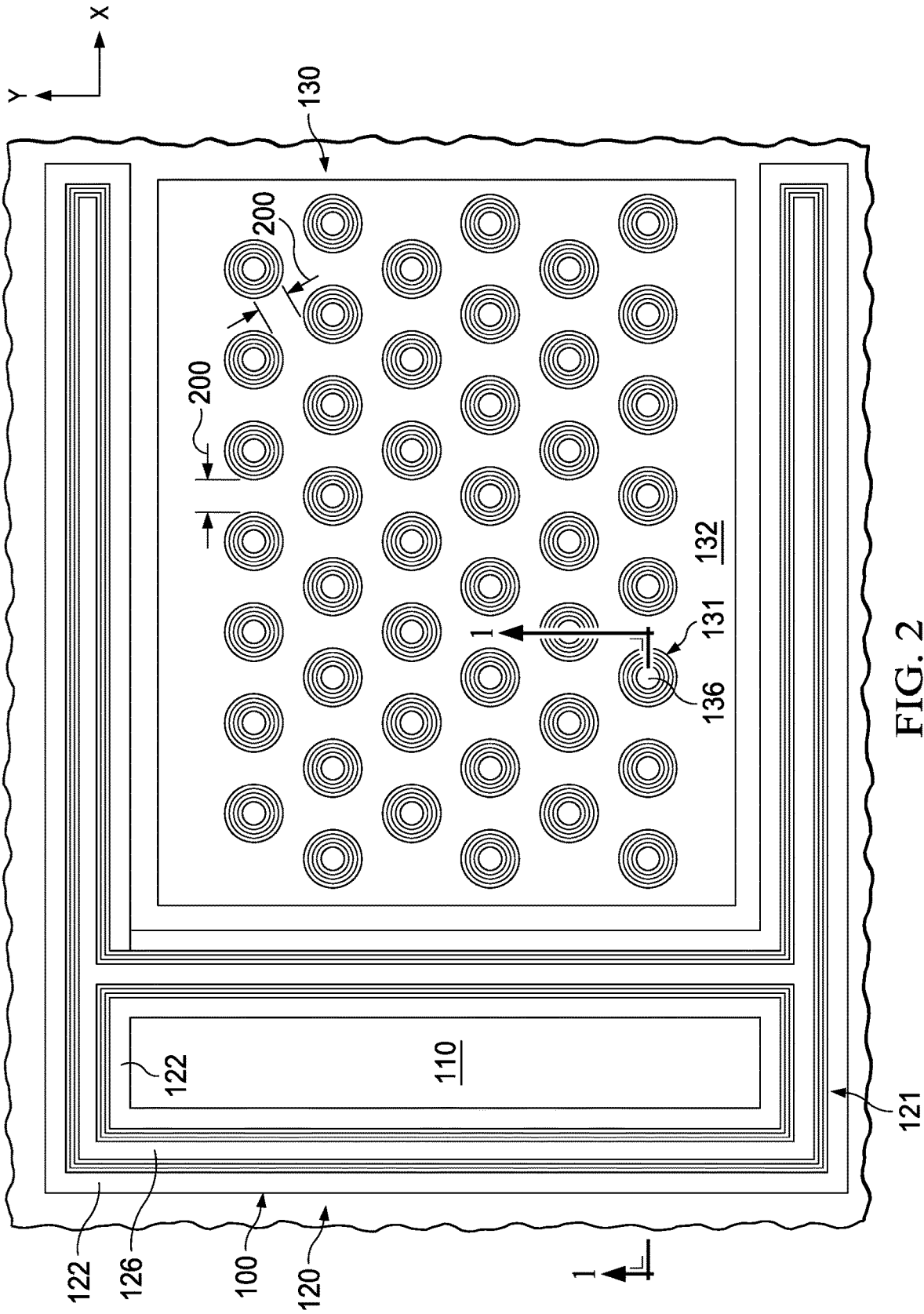
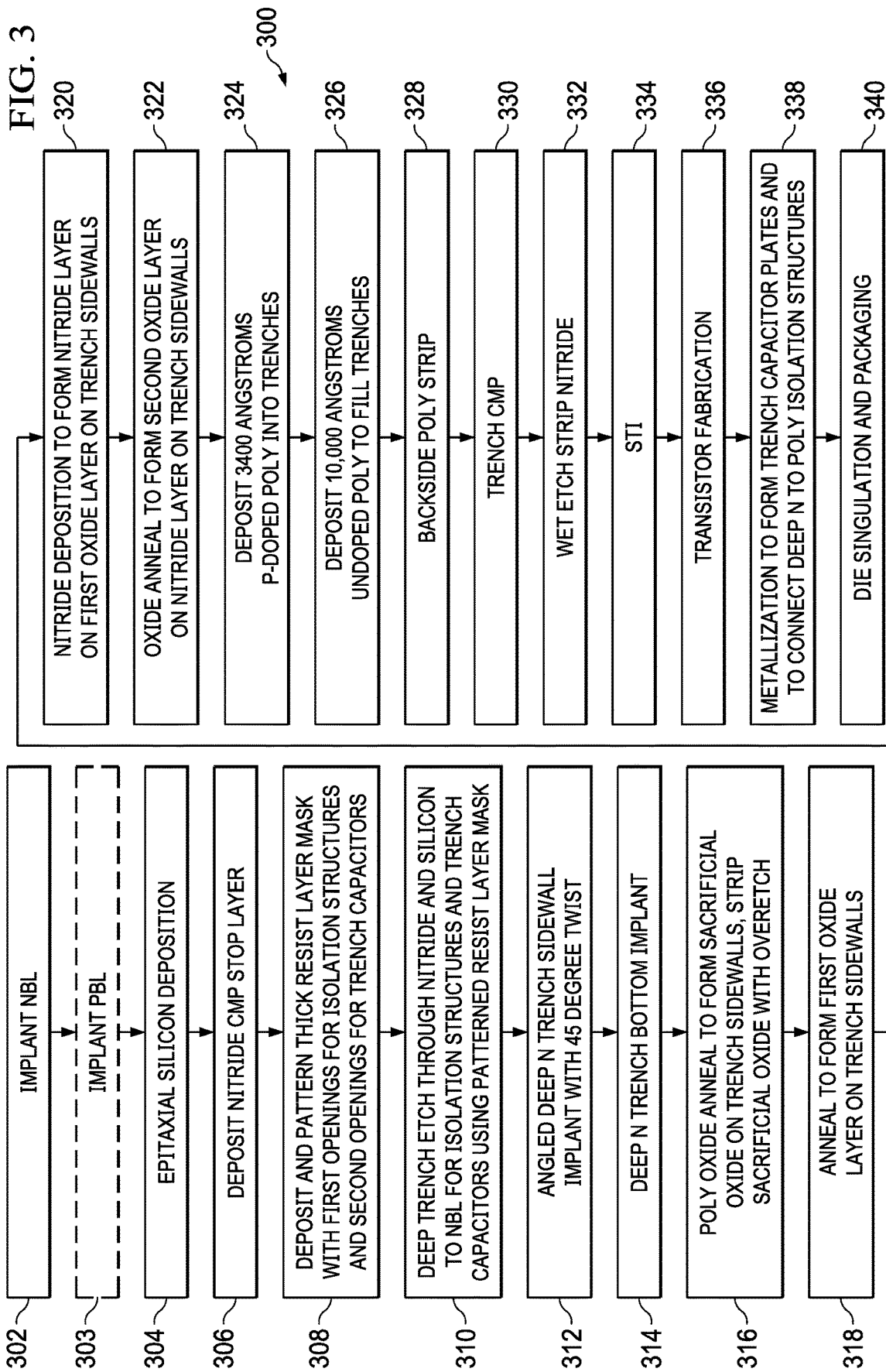


FIG. 2



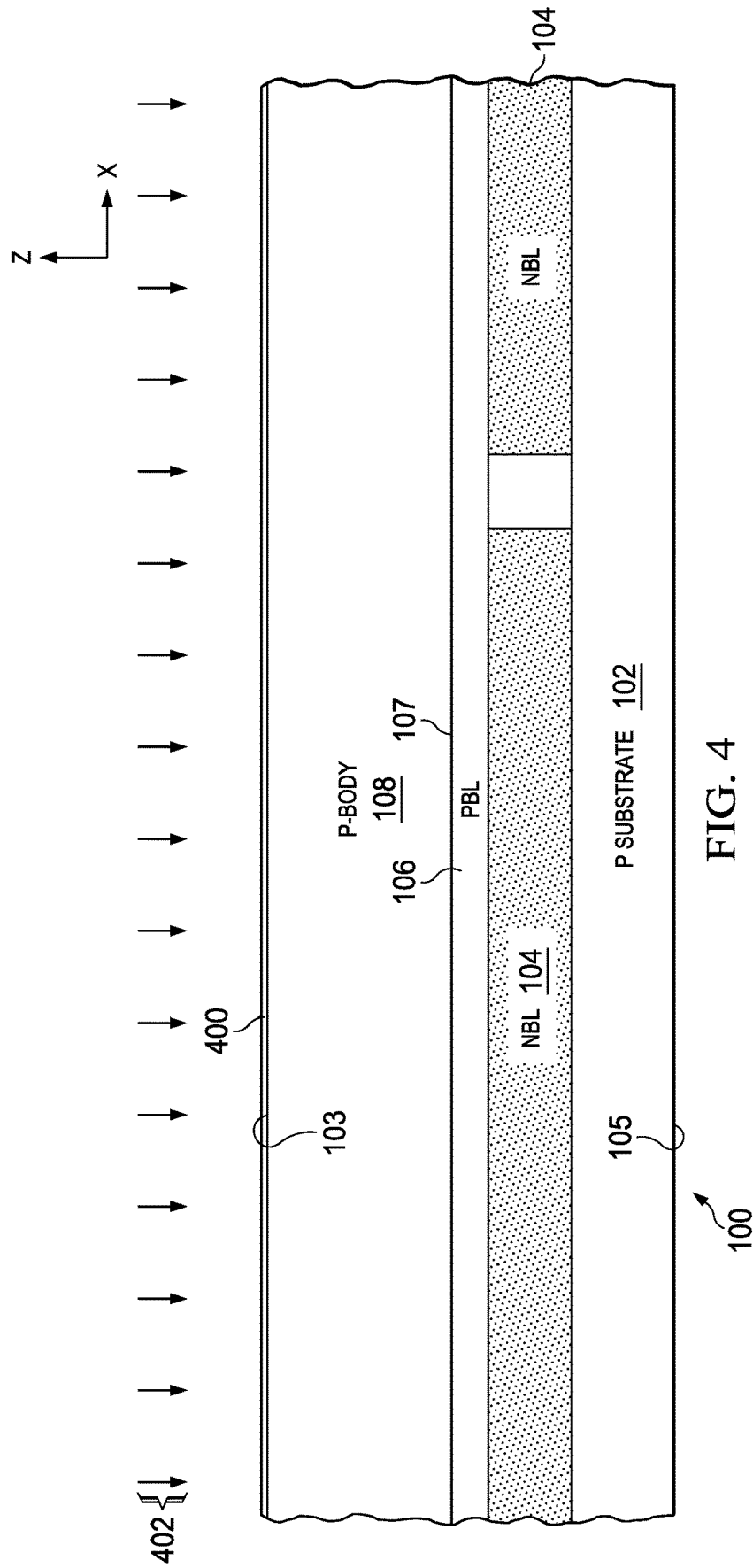


FIG. 4

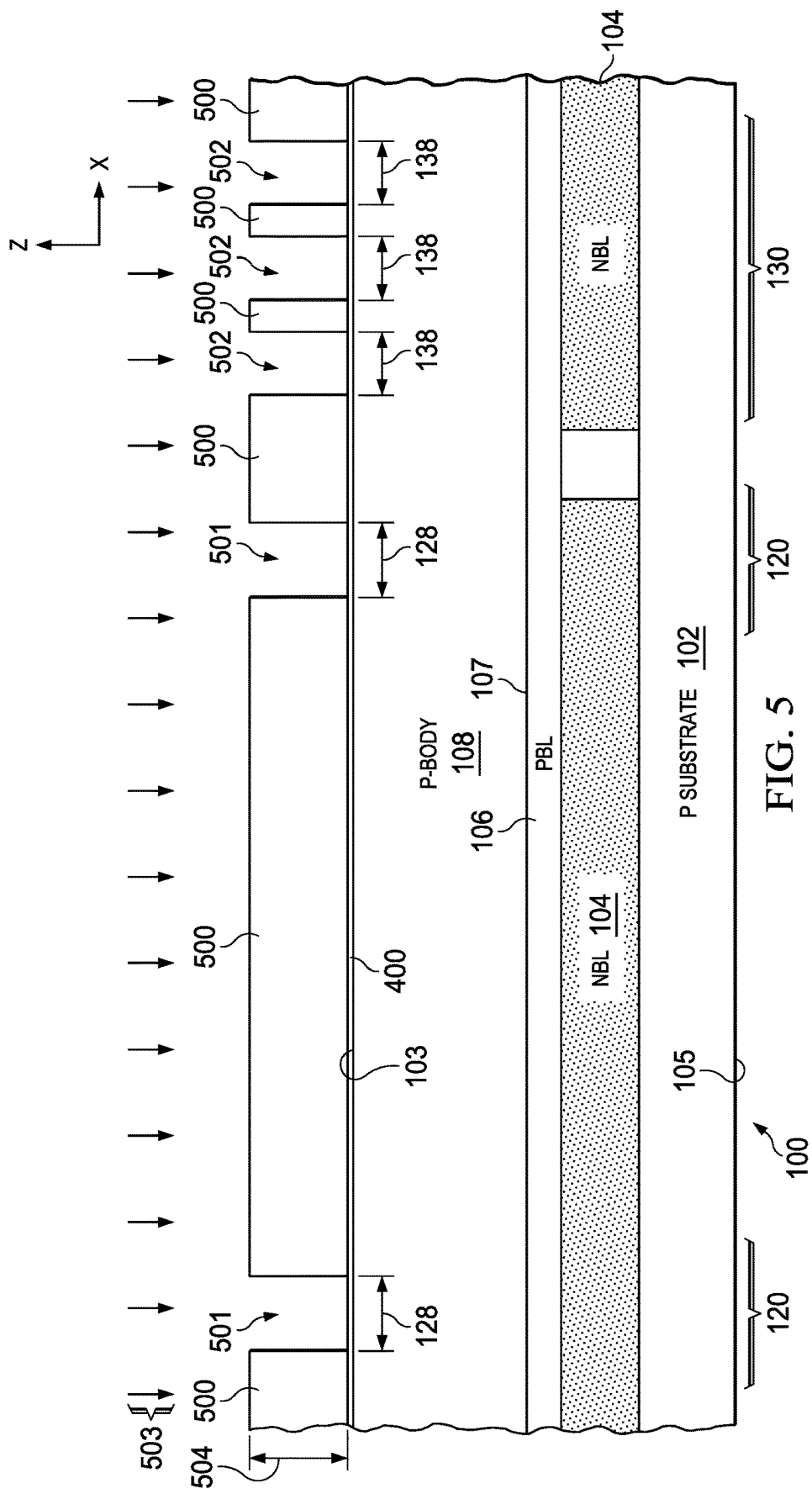


FIG. 5

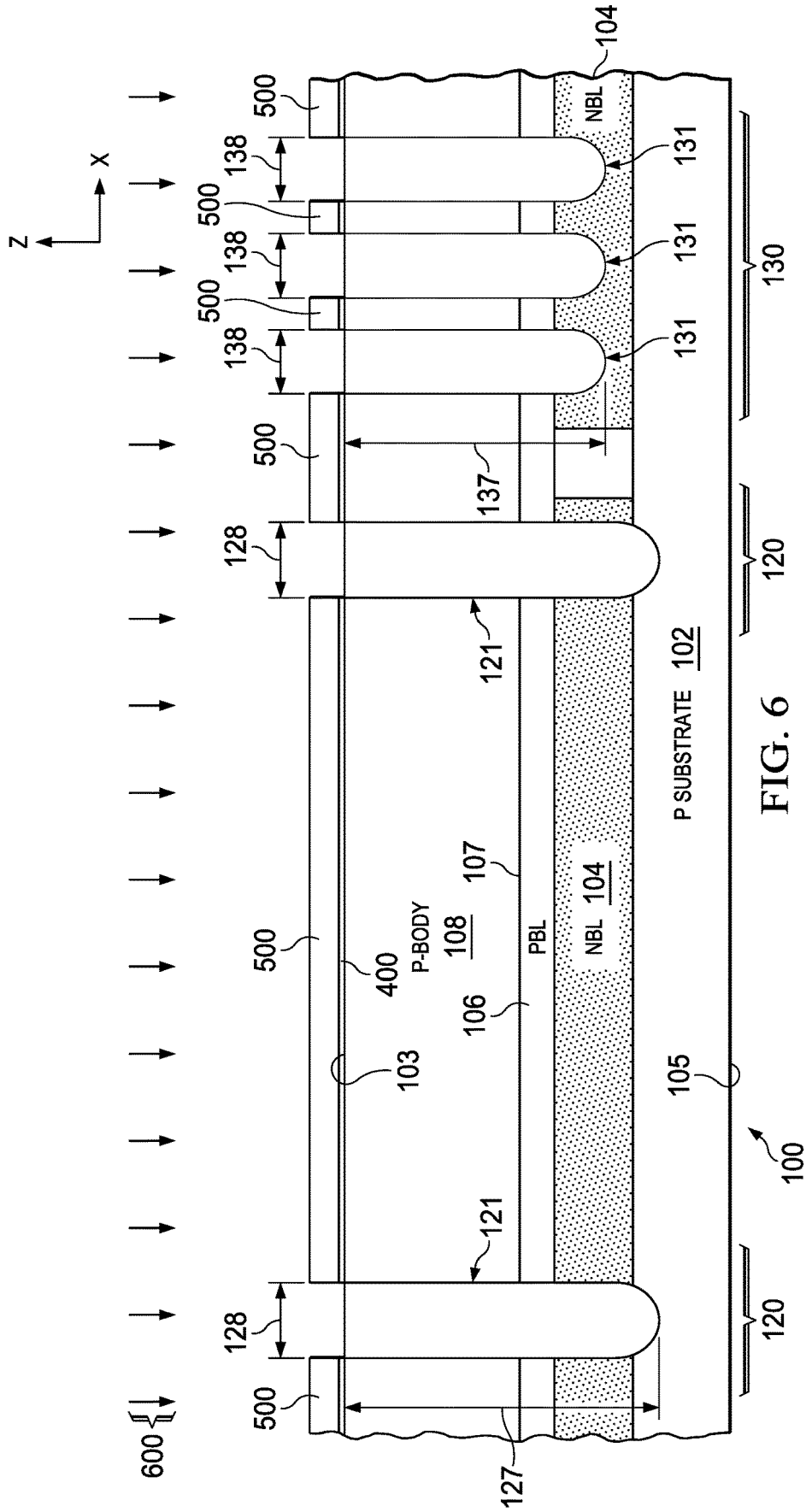


FIG. 6

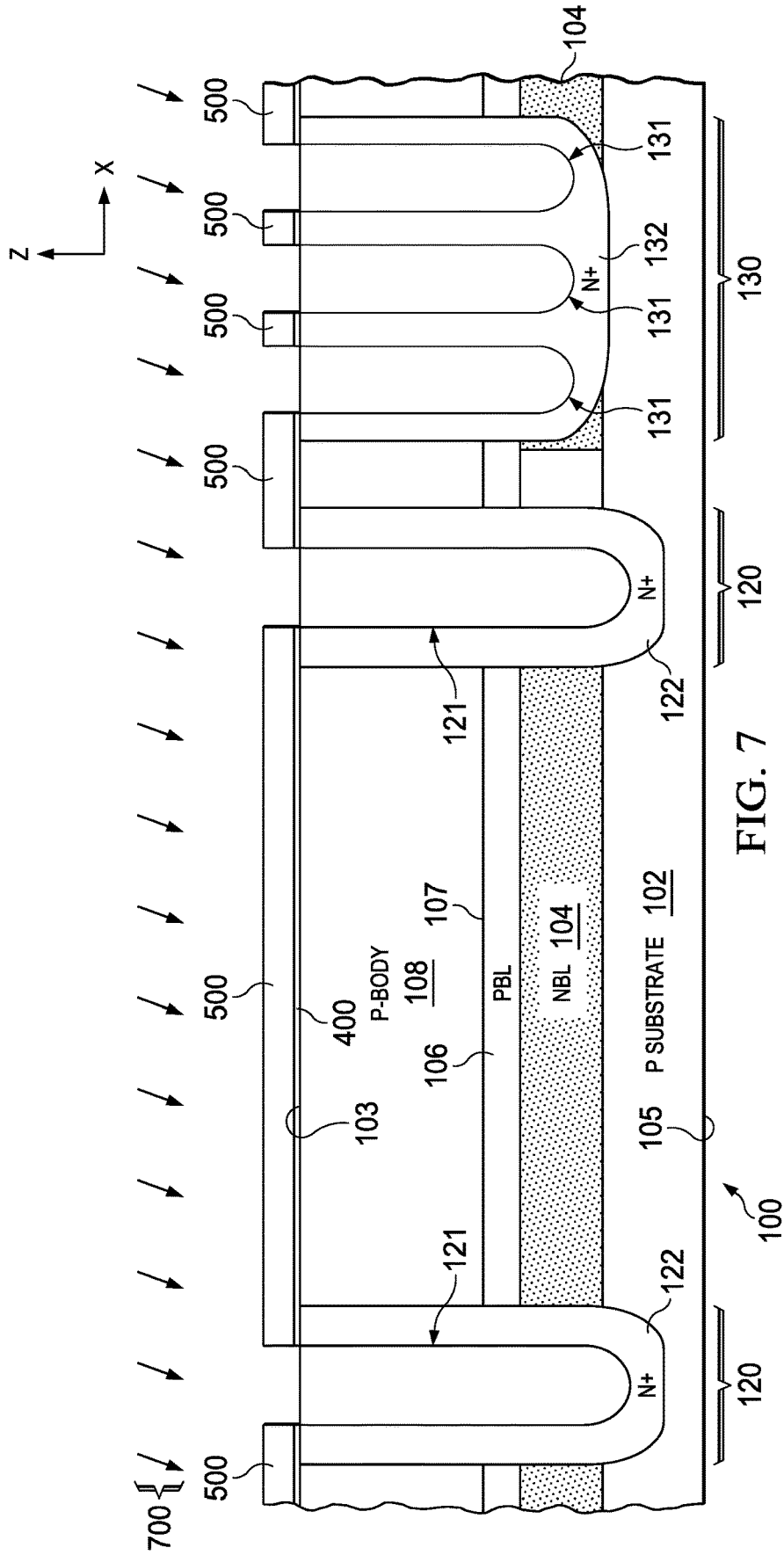


FIG. 7

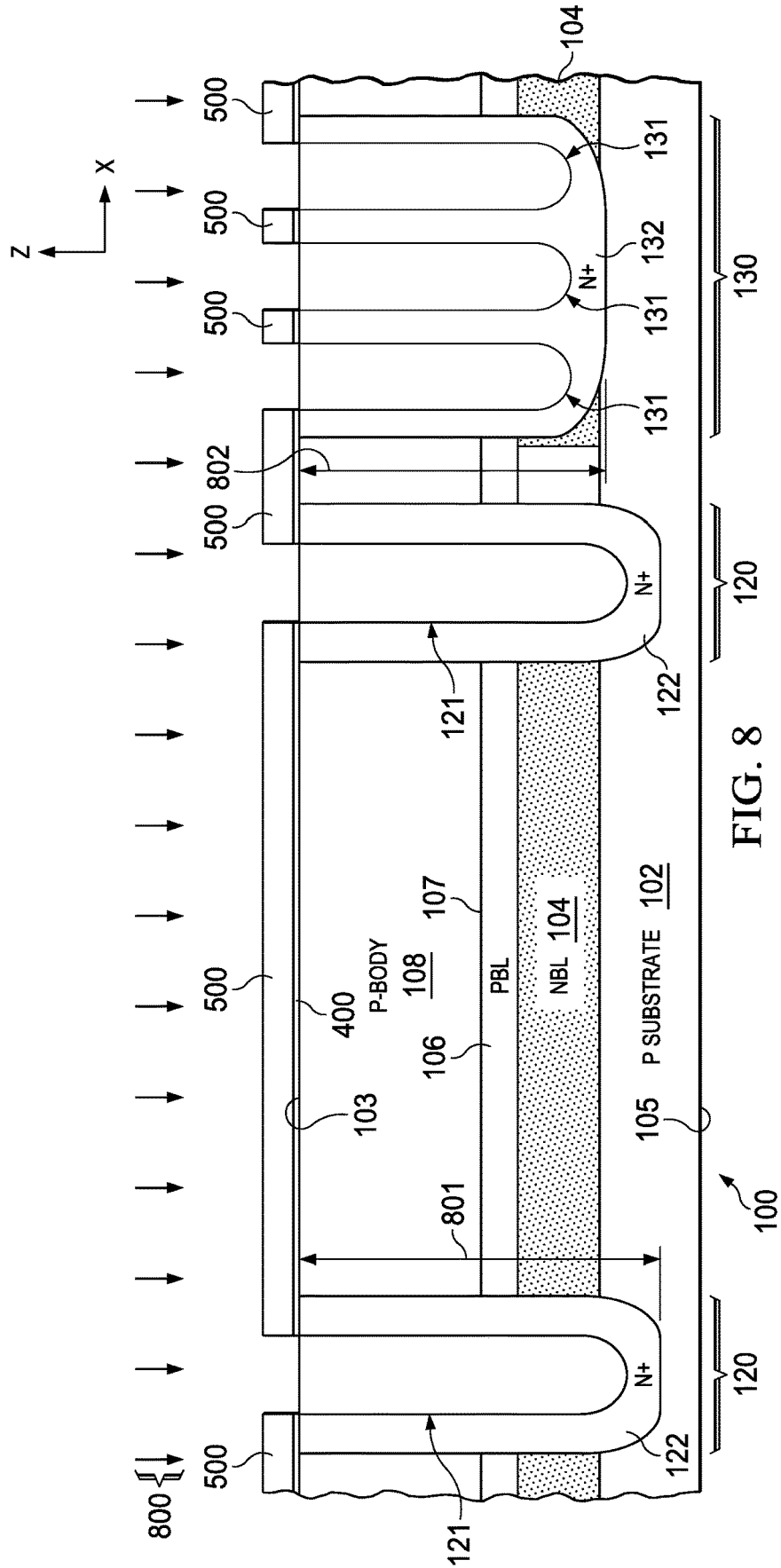


FIG. 8

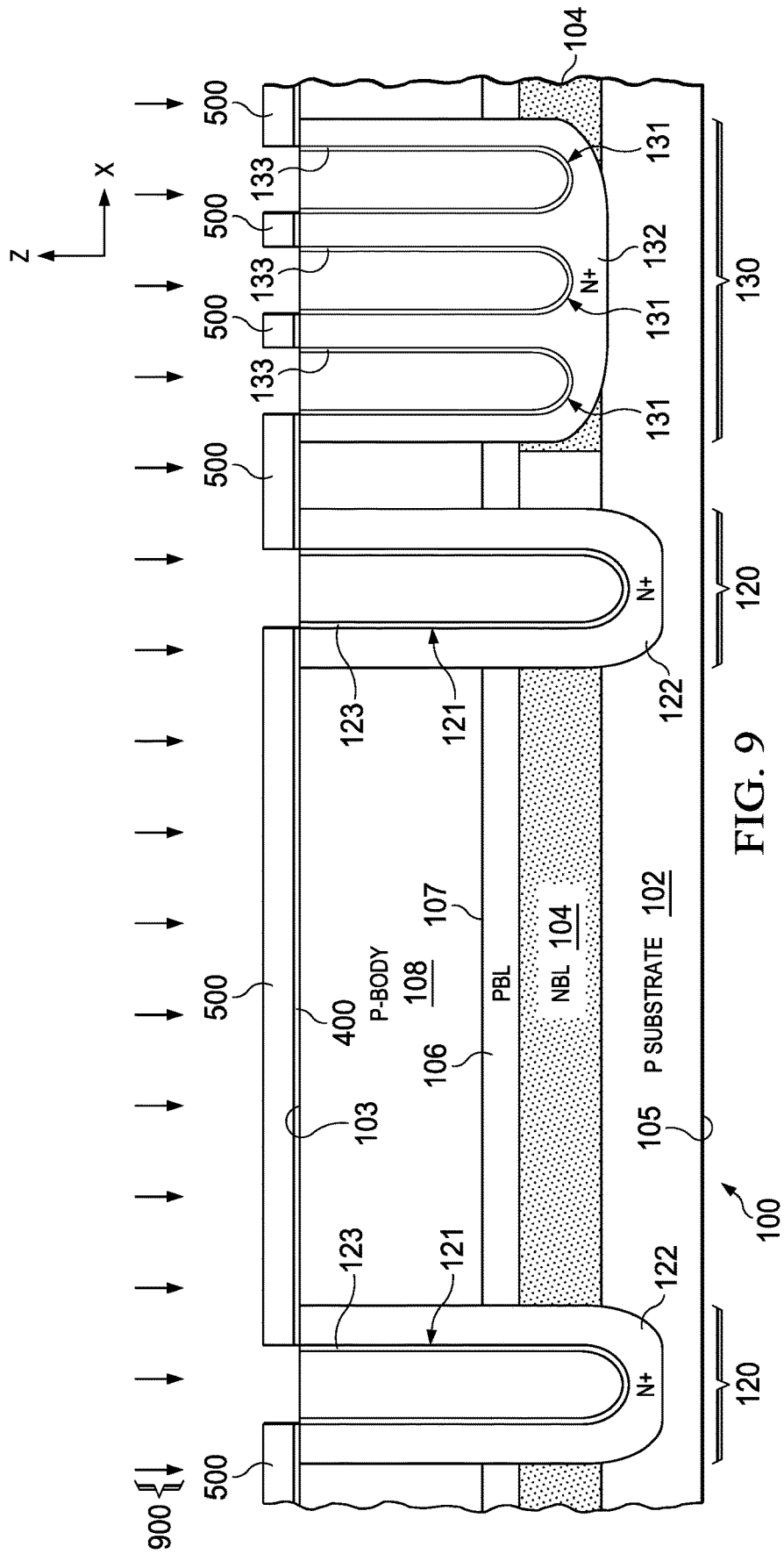
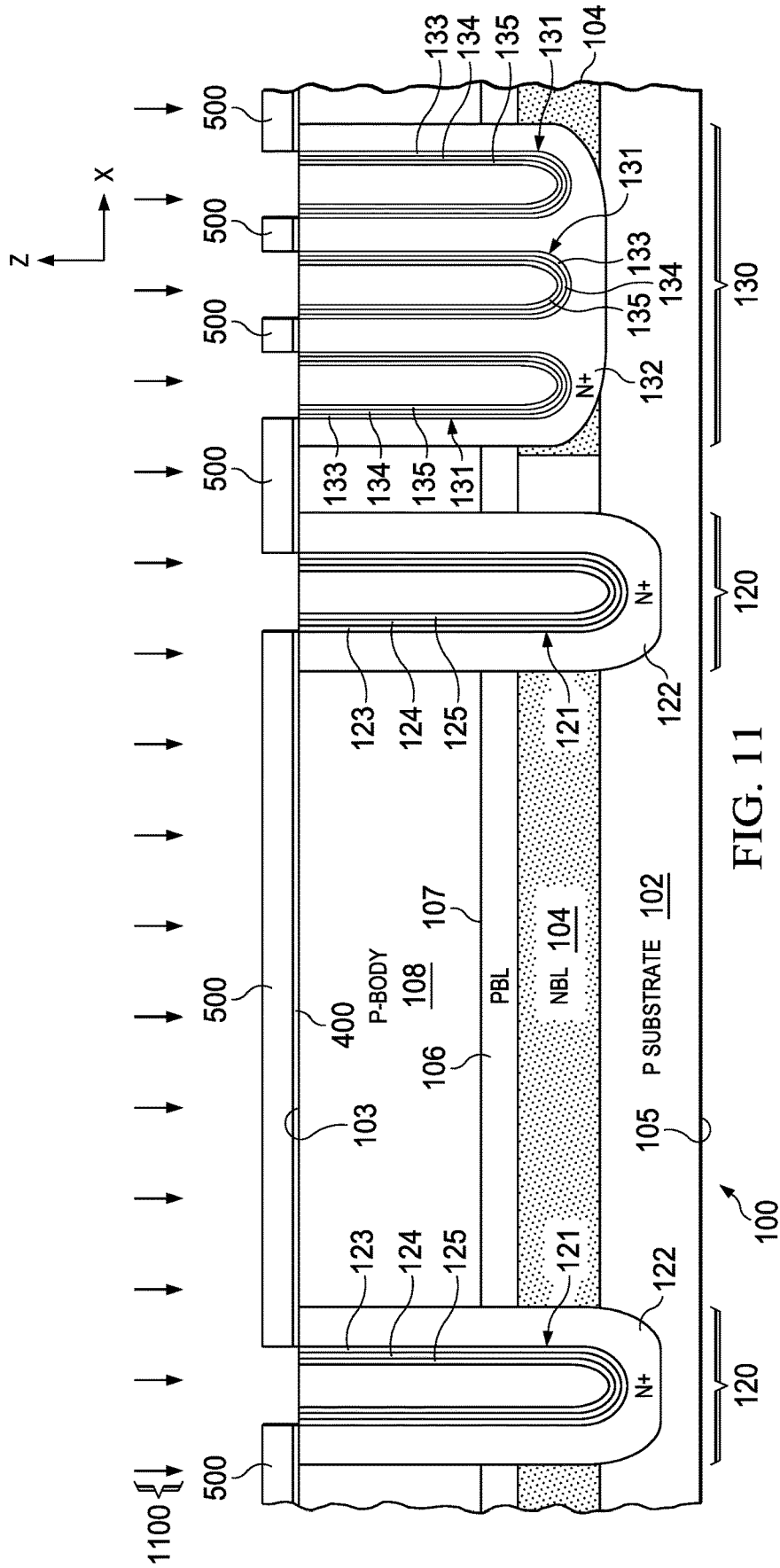
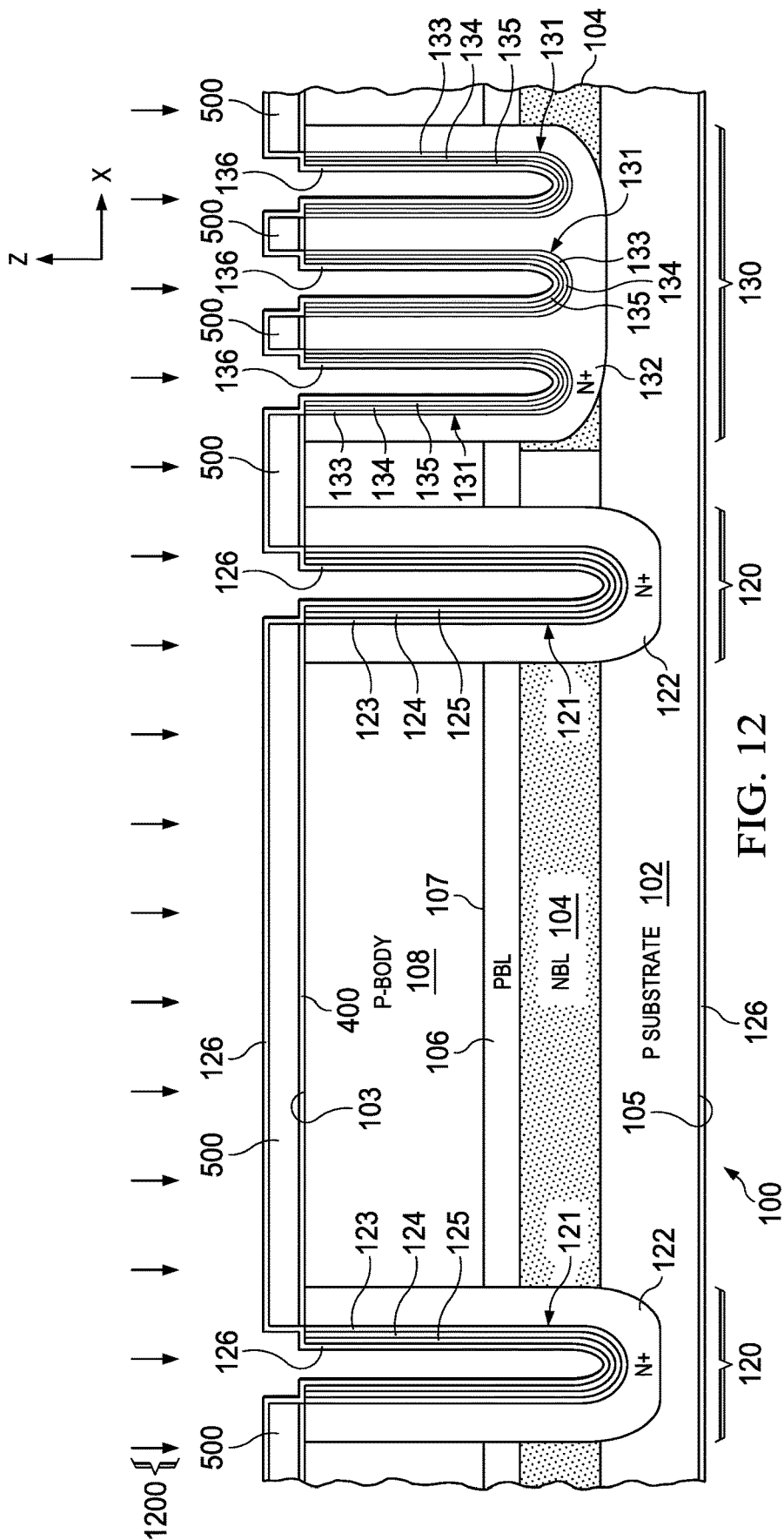


FIG. 9





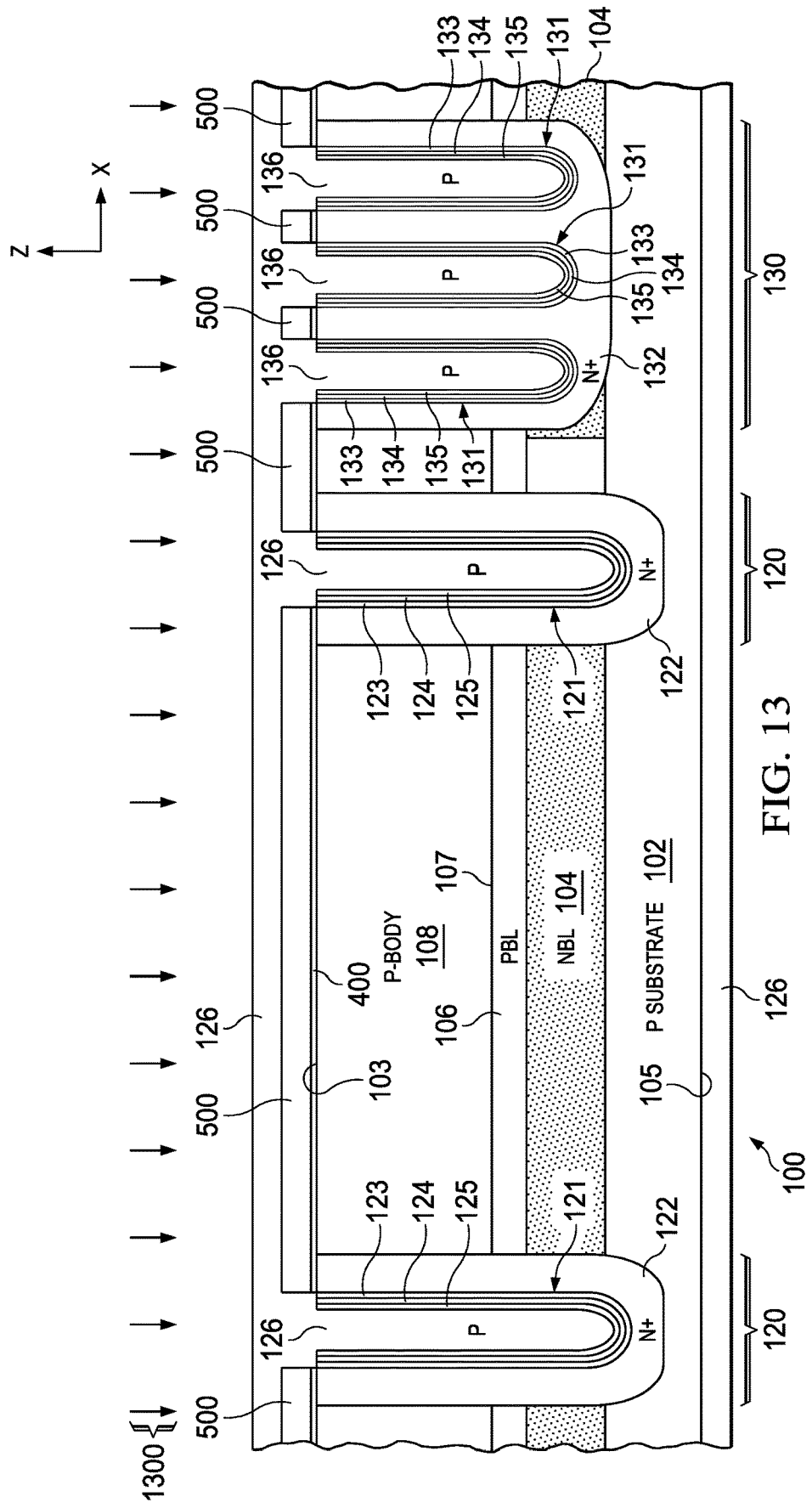


FIG. 13

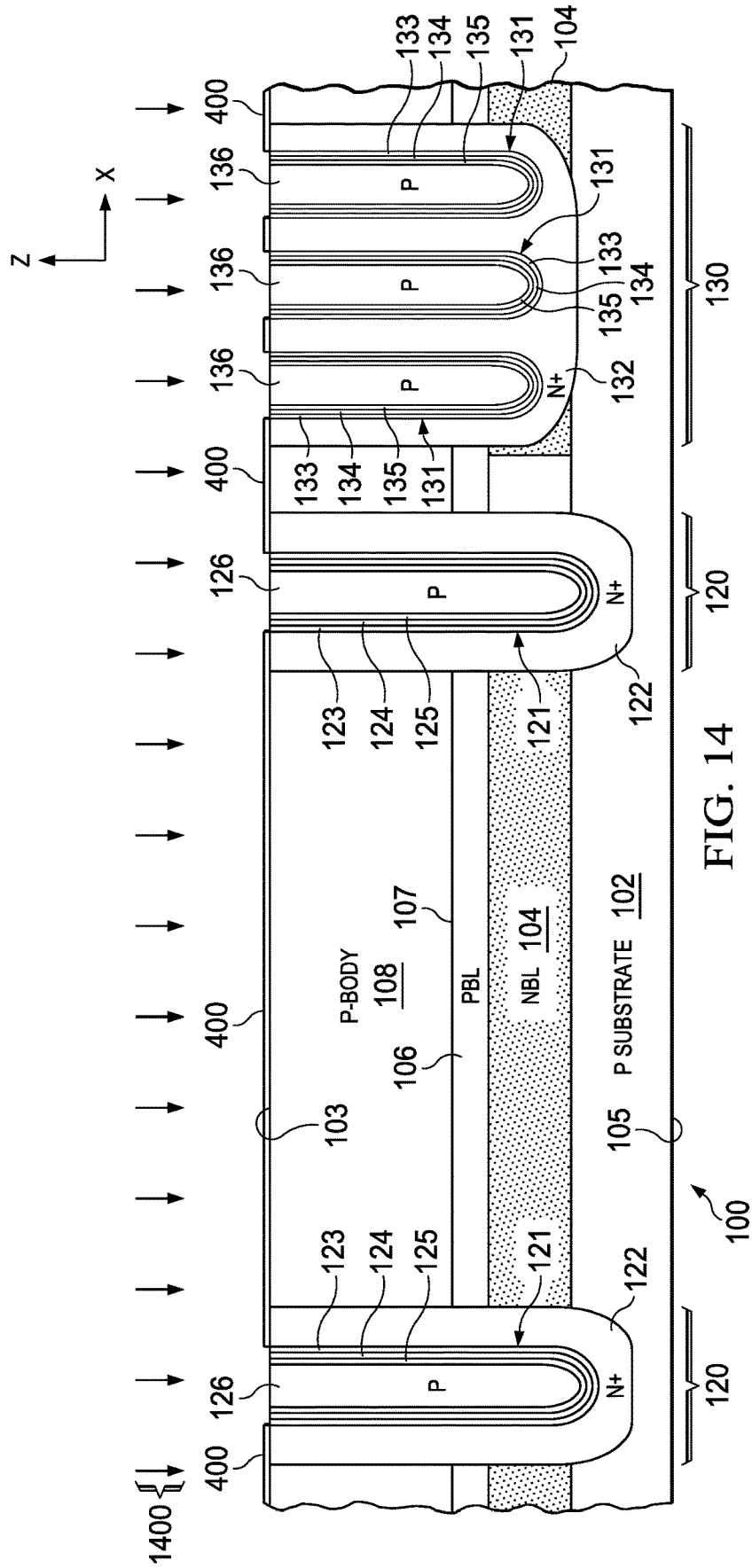


FIG. 14

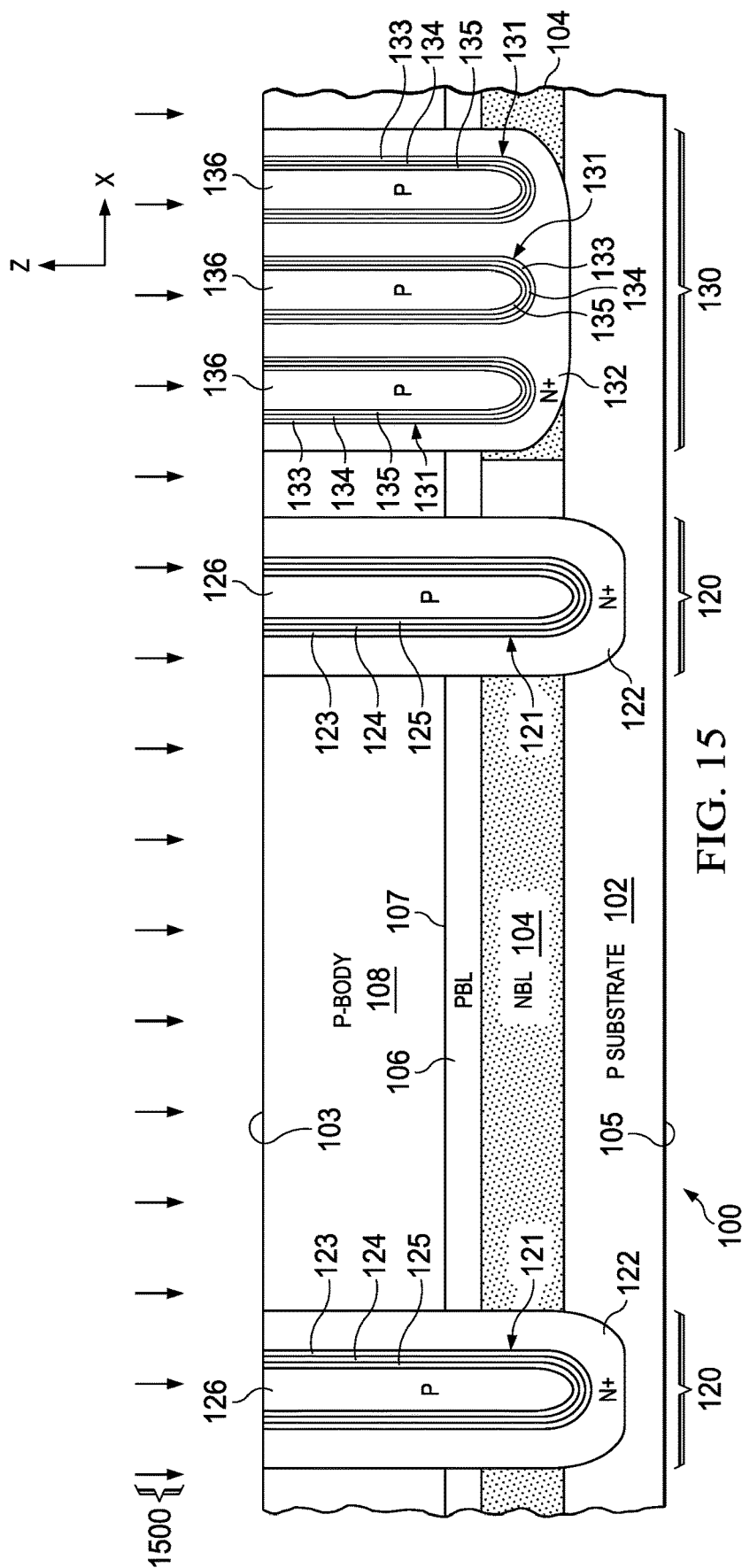


FIG. 15

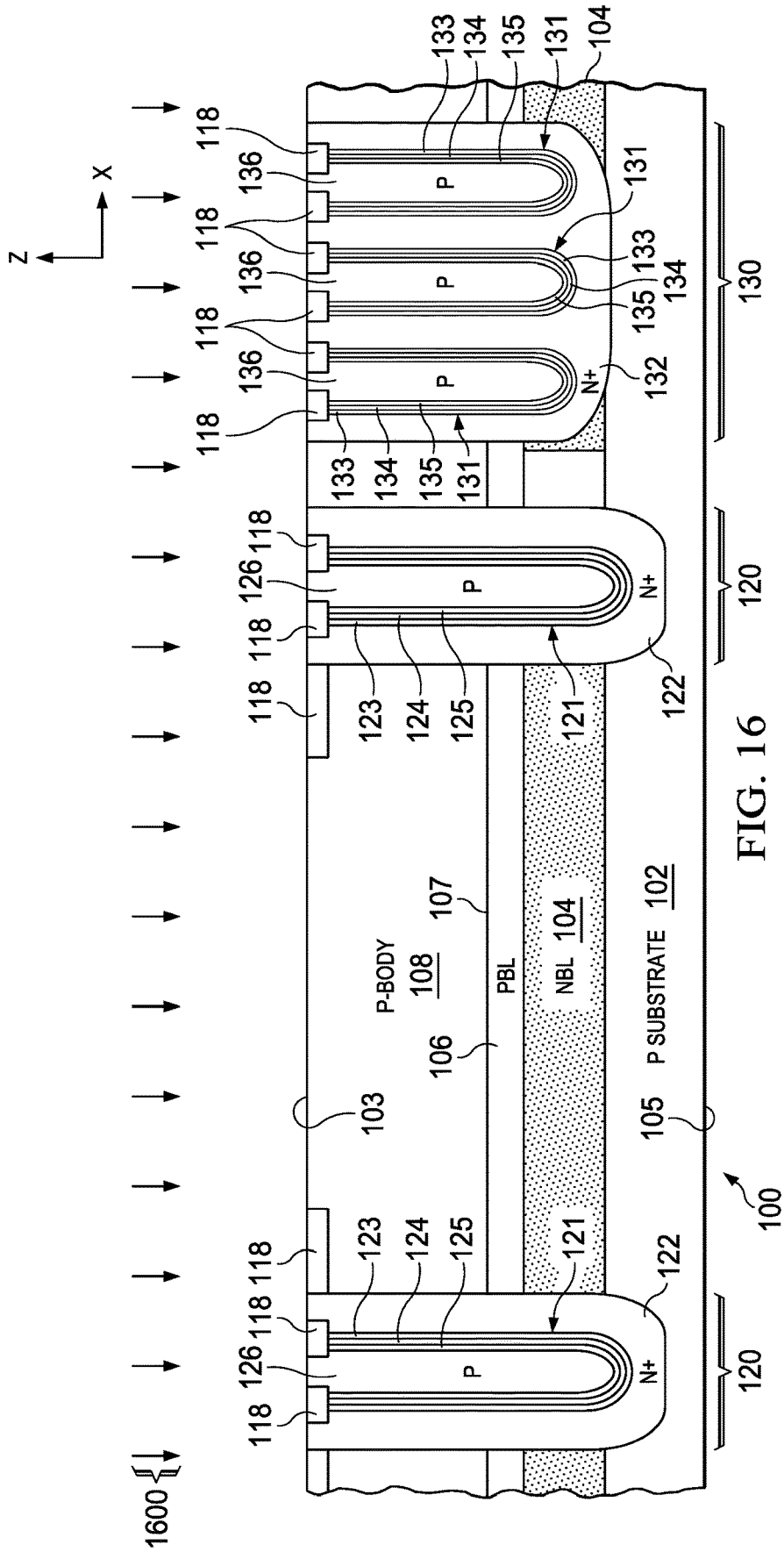


FIG. 16

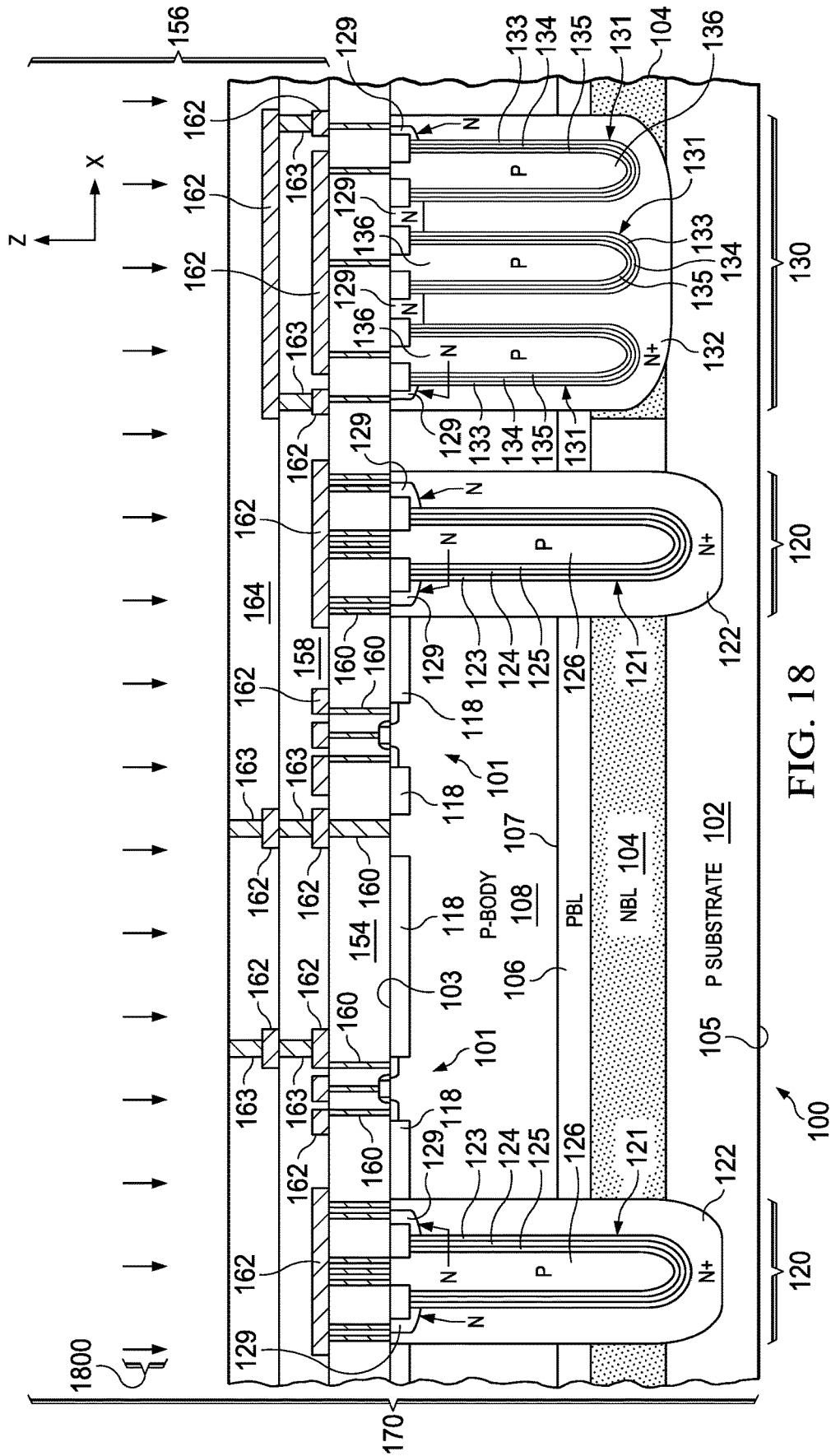


FIG. 18

SEMICONDUCTOR DEVICE WITH DEEP TRENCH ISOLATION AND TRENCH CAPACITOR

CROSS-REFERENCE TO RELATED APPLICATIONS

[0001] This application is a division of U.S. application Ser. No. 16/232,322 filed Dec. 26, 2018, the contents of which are herein incorporated by reference in its entirety.

FIELD

[0002] This disclosure relates to semiconductor devices with isolation structures and capacitors.

BACKGROUND

[0003] Isolation structures are used in integrated circuits to provide an electrically isolated active region for one or more transistors or other circuit components, and allow the use of different power supply domains on a single IC (e.g., high and low voltage circuits). One form of isolation structures is deep trench isolation. Deep trenches are also used to form trench capacitors in integrated circuits. Conventional semiconductor device fabrication processes separately manufacture trench isolation and trench capacitors, requiring separate masking and other process steps, and increasing cost and process complexity.

SUMMARY

[0004] This summary is provided to introduce a brief selection of disclosed concepts in a simplified form that are further illustrated and described below. This summary is not intended to limit the scope of the claimed subject matter. Disclosed aspects include semiconductor devices and fabrication methods therefor. An example semiconductor device includes an isolation structure and a trench capacitor formed using a single resist mask for etching corresponding first and second trenches. In one example, the trenches include dielectric liners formed on the trench sidewalls, and are filled with polysilicon. Deep doped regions extend around the trenches. In one example, the trenches and the deep doped regions extend from a semiconductor surface layer to a buried layer of a semiconductor structure. Conductive features of a metallization structure connect the polysilicon of the isolation trench to the deep doped region to form an isolation structure. Second conductive features of the metallization structure connect to the polysilicon of the capacitor trench to form a first capacitor plate, and further conductive features of the metallization structure are connected to the deep doped region around the capacitor trench to form a second capacitor plate. In one example, the isolation trench width is different from the capacitor trench width. In one example, the isolation and capacitor trenches have different depths. In one example, the trenches include multilayer dielectric liners, such as oxide, nitride and oxide (ONO) sublayers. In one example, capacitor includes multiple trenches surrounded by the second deep doped region and individually including a corresponding dielectric sidewall liner and polysilicon fill. In certain example, the trench polysilicon is doped. One example also includes a shallow implant region that extends in the semiconductor surface layer along a side of the isolation trench within the deep doped region.

[0005] A method is disclosed for fabricating an isolation structure in a semiconductor device. An example method includes forming a trench in a semiconductor structure forming a deep doped region surrounding the trench, forming a dielectric on a sidewall of the trench, filling the trench with polysilicon, and forming conductive features of a metallization structure that connect the polysilicon to the deep doped region to form an isolation structure. In one example, the dielectric is formed as a multi-layer dielectric liner by depositing a first oxide layer on the sidewall of the trench, depositing a nitride layer on the first oxide layer, and depositing a second oxide layer on the nitride layer. In one example, the method further includes forming a shallow implant region along a side of the trench within the deep doped region.

[0006] A disclosed method of fabricating a semiconductor device includes forming a resist layer with a first opening and a second opening on a top surface of a semiconductor structure, etching through the first opening to form a first trench and etching through the second opening to form a second trench, and implanting dopants through the first opening to form a first deep doped region surrounding the first trench and through the second opening to form a second deep doped region surrounding the second trench. The method further includes depositing a first dielectric liner through the first opening and through the second opening, and depositing polysilicon through the first and second openings to fill the trenches. The method further includes forming first conductive features of a metallization structure that connect the first polysilicon to the first deep doped region to form an isolation structure, as well as forming second conductive features of the metallization structure that connect to the second polysilicon to form a first capacitor plate, and forming further conductive features of the metallization structure that connect to the second deep doped region to form a second capacitor plate. In one example, the resist layer formation includes patterning the first opening with a first width, and patterning the second opening with a smaller second width. In this example, the first trench has a larger depth than the second trench. In one example, the dielectric liners are formed as multi-layer structures by performing deposition processes through the mask openings that deposit a first oxide layer on the sidewalls of the trenches, deposit a nitride layer on the first oxide layer, and deposit (or grow oxide on nitride to form oxynitride) a second oxide layer on the nitride layer. In one example, the method further includes forming a shallow implant region along a side of the trench within the deep doped region before an ONO deposition.

BRIEF DESCRIPTION OF THE DRAWINGS

[0007] FIG. 1 is a partial sectional side elevation view of an integrated circuit semiconductor device that includes deep trench isolation structures and trench capacitors.

[0008] FIG. 2 is a top plan view of a portion of the semiconductor device of FIG. 1.

[0009] FIG. 3 is a flow diagram showing a method for making a semiconductor device and for making an isolation structure in a semiconductor device.

[0010] FIGS. 4-18 are partial sectional side elevation views of the integrated circuit of FIGS. 1 and 2 at various stages of fabrication according to the method of FIG. 3.

DETAILED DESCRIPTION

[0011] In the drawings, like reference numerals refer to like elements throughout, and the various features are not necessarily drawn to scale. In the following discussion and in the claims, the terms “including”, “includes”, “having”, “has”, “with”, or variants thereof are intended to be inclusive in a manner similar to the term “comprising”, and thus should be interpreted to mean “including, but not limited to . . .” Also, the term “couple” or “couples” is intended to include indirect or direct electrical or mechanical connection or combinations thereof. For example, if a first device couples to or is coupled with a second device, that connection may be through a direct electrical connection, or through an indirect electrical connection via one or more intervening devices and connections. The various features of the disclosed examples can be used in connection with a variety of different semiconductor devices, including without limitation integrated circuits having multiple electronic components, as well as single component semiconductor devices (e.g., single transistor products, single diode products, etc.).

[0012] Example devices and fabrication methods provide process integration for both trench isolation and high density trench capacitors fabricated using a shared resist mask to economize fabrication time and costs. In some examples, the trenches are etched, deep doped regions surrounding the trenches are implanted, and the trenches are lined and filled using a thick photoresist and hard mask patterned with openings for capacitor trenches and wider openings for isolation structure trenches. Described examples provide metallization layout structures to provide first and second capacitor plates for capacitor trench structures, and connected polysilicon and deep doped regions for isolation trench structures. Described examples facilitate forming deep trench isolation features as well as high density trench capacitor with one mask, and with reduced isolation (e.g., deep n region) to isolation spacing using self-aligned deep doped region implantation on deep trench sidewalls.

[0013] FIGS. 1 and 2 show an example integrated circuit semiconductor device 100 that includes two metal oxide semiconductor (MOS) transistors 101. Disclosed examples can also include stand-alone discrete transistor semiconductor devices that have a single transistor. The transistors 101 in FIG. 1 have single gate, source and drain finger structures. In other implementations, transistors can be built with multiple finger structures surrounding a center finger, such as source-centered configurations, drain-centered configurations, etc. The deep trench isolation and trench capacitor concepts of the present disclosure can be implemented in combination with any type or form of transistor, such as MOS transistors bipolar transistors, etc. In addition, various aspects of the disclosure can be used in combination with drain extended MOS transistors (not shown). Described examples include doped regions of various semiconductor structures which may be characterized as p-doped and/or n-doped regions or portions, and include regions that have majority carrier dopants of a particular type, such as n-type dopants or p-type dopants.

[0014] The transistors 101 are fabricated on and/or in a semiconductor substrate 102. The semiconductor substrate 102 in one example is a silicon wafer, a silicon-on-insulator (SOI) substrate or other semiconductor structure. In one example, the substrate 102 is a p-doped silicon substrate or wafer, with a first (e.g., top) side 103, various buried layers

104, 106 formed therein, and a second (e.g., bottom) side 105. In another possible implementation, the substrate 102 includes one or more epitaxial silicon layers (not shown) formed on a top surface, with one or more of the buried layers 104, 106 formed in epitaxial layers of the substrate. In the illustrated example, the substrate 102, the buried layers 104 and 106, and an upper semiconductor surface layer (e.g., body region 108) constitute a semiconductor structure. The example semiconductor structure includes a first doped layer 106 that includes p-type majority carrier dopants. In one implementation, the p-type layer includes a portion implanted with boron to form a p-type buried layer (PBL) with an upper or top side 107. The semiconductor surface layer 108 extends over (e.g., directly on) the p-type buried layer 106 and includes the upper side 103 of the semiconductor structure. The example layer 104 (e.g., an n-type buried layer or NBL) includes n-type majority carrier dopants. The NBL 104 extends along the vertical Z direction from beneath the PBL 106 toward the second side 105. In one example, a first epitaxial silicon layer is formed over the upper surface of a silicon wafer substrate 102, and all or a portion of the first epitaxial layer is implanted with n-type dopants (e.g., phosphorus, etc.) to form the NBL 104. In this example, a second epitaxial silicon layer is formed over the first epitaxial layer, and all or a portion of the second epitaxial layer is implanted with p-type dopants (e.g., boron, etc.) to form the p-type buried layer 106 with the upper side 107. In one example, the PBL region 106 is formed using ion implantation through the first EPI surface. The example surface layer 108 has p-type majority carrier dopants and extends downward along the Z direction from the first side 103.

[0015] The transistors 101 are formed on or in the semiconductor surface layer 108 within an active region 110 of the semiconductor structure 102, 104, 106, 108. The example semiconductor surface layer 108 includes p-type majority carrier dopants. The illustrated device 100 includes an outer oxide isolation structure 118 that encircles the transistor 101 along the first (e.g., top) side 103 in the semiconductor surface layer 108. The oxide structure 118 in one example is a shallow trench isolation (STI) structure, which is disposed laterally outward of the transistors 101. In the illustrated example, the STI structure 118 defines an end of the active region 110 of the semiconductor substrate 102 in which the transistors 101 are formed.

[0016] The illustrated device 100 includes a trench-based isolation structure 120, referred to as a deep trench isolation structure. The deep trench isolation structure 120 in FIG. 1 is adjacent to the STI structure 118, and laterally encircles or surrounds the transistors 101 and the active region 110 of the semiconductor structure. The isolation structure 120 includes a first trench 121 that extends downward from the first side 103 through the semiconductor structure 102, 104, 106, 108 to the buried layer 104. The isolation structure 120 also includes a first deep doped region 122 with n-type majority carrier dopants (e.g., phosphorus). The first deep doped region 122 surrounds the first trench 121 and extends from the semiconductor surface layer 108 to the buried layer 104.

[0017] The isolation structure 120 also includes a first dielectric liner that extends along the sidewall of the first trench 121 from the semiconductor surface layer 108 to the buried layer 104. Any single or multilayer dielectric liner can be used. In one example, the first dielectric liner includes

a first oxide layer **123**, a nitride layer **124**, and a second oxide layer **125**. The first oxide layer **123** (e.g., silicon dioxide or SiO₂) extends along the sidewall of the first trench **121** from the semiconductor surface layer **108** to the buried layer **104**. The nitride layer **124** (e.g., silicon nitride or silicon oxynitride) extends along the first oxide layer **123** from the semiconductor surface layer **108** to the buried layer **104**. The second oxide layer **125** (e.g., silicon dioxide or SiO₂) extends along the nitride layer **124** from the semiconductor surface layer **108** to the buried layer **104**.

[0018] The isolation structure **120** also includes a first polysilicon **126** that extends inside the first dielectric liner **123**, **124**, **125**. The first polysilicon **126** fills the first trench **121** to the top side **103** of the semiconductor surface layer **108**. The first polysilicon **126** in one example includes p-type majority carrier dopants (e.g., boron). In the example of FIGS. **1** and **2**, the deep trench isolation structure **120** is formed as a ring structure that laterally surrounds the transistors **101**. As shown in FIG. **1**, the first trench **121** has a first depth **127** and a first width **128**. The semiconductor device **100** also includes shallow implant regions **129** with n-type majority carrier dopants (e.g., a shallow n-well implanted with phosphorus). The shallow implant regions **129** extend in the semiconductor surface layer **108** along a side of the first trench **121** within the first deep doped region **122**. In one example, the shallow implant is also used to form lower case n-type source/drain features (not shown) of transistors in the device **100**.

[0019] The illustrated device **100** also includes one or more trench-based capacitors. In one example, the trench capacitor **130** can be constructed using a single trench. In the example of FIGS. **1** and **2**, the capacitor **130** includes multiple second trenches **131** that individually extend through the semiconductor structure **102**, **104**, **106**, **108** to the buried layer **104**. Each of the second trenches **131** is surrounded by a second deep doped region **132**. FIG. **1** shows three trenches **131** that extend from the first side **103** through the semiconductor structure to the buried layer **104**. The second trench **131** has a second depth **137** and a second width **138**. The first width **128** of the first (isolation) trench **121** is greater than the second (capacitor trench) width **138** in the device of FIGS. **1** and **2**. The first width **128** of the first trench **121** is greater than the second width **138** of the capacitor trenches **131**. In one example, the first width **128** of the first trench **121** is approximately 1.5 μm, for example, from 1.35 μm to 1.65 μm, and the second width **138** of the capacitor trenches **131** is approximately 1.2 μm, for example, from 1.05 μm to 1.35 μm.

[0020] The example capacitor **130** further includes second dielectric liners (e.g., layers **133**, **134**, and **135**) in each of the trenches **131**. The second dielectric liners extend along sidewalls of the second trenches **131** from the semiconductor surface layer **108** to the buried layer **104**. The example second dielectric liner is a multi-layer structure with a third oxide layer **133** that extends along the sidewall of the second trench **131** from the semiconductor surface layer **108** to the buried layer **104**. The example second dielectric liner also includes a second nitride layer **134** that extends along the third oxide layer **133** from the semiconductor surface layer **108** to the buried layer **104**, and a fourth oxide layer **135** that extends along the second nitride layer **134** from the semiconductor surface layer **108** to the buried layer **104**.

[0021] The capacitor **130** also includes a second deep doped region **132** implanted with n-type majority carrier

dopants (e.g., phosphorus). The second deep doped region **132** surrounds the second trenches **131** and extends from the semiconductor surface layer **108** to the buried layer **104**. In addition, the capacitor **130** includes a second polysilicon **136** with p-type majority carrier dopants (e.g., boron). The second polysilicon **136** extends inside the second dielectric liner **133**, **134**, **135** and fills the second trench **131** to the top side **103** of the semiconductor surface layer **108**. The capacitor **130** also includes a shallow implant region **129** having majority carrier dopants of the second conductivity type. The shallow implant region **129** extends in the semiconductor surface layer **108** between the second trenches **131** within the second deep doped region **132**.

[0022] The semiconductor device **100** includes a metallization structure that extends over the semiconductor surface layer **108**. The metallization structure includes conductive features that connect the first polysilicon **126** to the first deep doped region **122** for the trench-based isolation structures **120**, as well as second conductive features connected to the second polysilicon **136** to form a first capacitor plate, and further conductive features connected to the second deep doped region **132** to form a second capacitor plate of the capacitor **130**. The metallization structure includes a first dielectric structure layer **154** formed over the semiconductor structure, and a multi-level upper metallization structure **156**. In one example, the first dielectric **154** structure layer is a pre-metal dielectric (PMD) layer disposed over the transistors **101** and the upper surface of the semiconductor structure. In one example, the first dielectric structure layer **154** includes silicon dioxide (SiO₂) deposited over the transistors **101**, the semiconductor surface layer **108** and the STI structures **118**. The metallization structure **154**, **156** covers the transistors **101** and provides internal and/or external electrical interconnection to the transistor source, drain and gate terminals.

[0023] The PMD layer **154** includes contact structures **160** (e.g., tungsten) that provide direct electrical connection (e.g., direct contact or connection through a silicide layer such as CoSi₂, not shown) to one or more features of the transistors **101**. The PMD material layer **154** is formed over the illustrated structure, with contact structures **160** formed therein to provide electrical interconnection access for one or more further upper metallization layers **158** and **164-168**. In one example, a silicide is formed over the top surfaces of the source, drain and gate electrode structures of the transistors **101**, and over the tops of the polysilicon features **126**, **136** and to the deep doped regions **122**, **132**. Contacts **160** of the PMD layer **154** are connected to the polysilicon features **126**, **136** and to the deep doped regions **122**, **132** of the isolation structure **120** and the capacitor **130**.

[0024] The upper metallization structure **156** includes one or more layers. In the illustrated example, the upper metallization structure **156** includes a first metallization layer **158** formed over the PMD layer **154**, as well as further metallization layers **164**, **165**, **166**, **167**, and **168** progressively formed over the preceding layer as shown in FIG. **1**. The device **100** in FIGS. **1** and **2** is shown as a wafer **170** prior to singulation and packaging, but the illustrated structure represents the described features after separated as a die for packaging. Although the example die **170** is an integrated circuit with multiple components, such as transistors **101**, other stand-alone discrete semiconductor device implemen-

tations can include a single transistor or other electronic component with an isolation structure **120** and at least one capacitor **130**.

[0025] The upper metallization structure **156** is a 6 layer with a first layer **158**, referred to herein as an interlayer or interlevel dielectric (ILD) layer. Different numbers of layers can be used in different implementations. In one example, the first ILD layer **158**, and the other ILD layers of the upper metallization structure **156** are formed of silicon dioxide (SiO_2) or other suitable dielectric material. In certain implementations, the individual layers of the multi-layer upper metallization structure **156** are formed in two stages, including an intra-metal dielectric (IMD, not shown) sub layer with conductive metal routing features or lines **162** (e.g., aluminum, copper, etc.), and an ILD sublayer overlying the IMD sub layer with conductive contacts or plugs **163** (e.g., tungsten vias). The individual IMD and ILD sublayers can be formed of any suitable dielectric material or materials, such as SiO_2 -based dielectric materials. The first layer **158**, and the subsequent layers in the upper metallization structure **156** include conductive metallization interconnect structures **162**, referred to as lines, formed on the top surface of the underlying layer. In this example, the first layer **158** and the subsequent ILD layers also include conductive vias **163**, such as tungsten or aluminum that provide electrical connection from the metallization features **162** of an individual layer to an overlying metallization layer.

[0026] The example of FIG. 1 includes a second layer **164** disposed over the first layer **158**. The ILD layer **158** includes conductive interconnect structures **162** and vias **163**. The structures **162**, **163** can be the same metal or different metals in various implementations. The individual layers can be constructed using any suitable metallization fabrication processes, such as single damascene or dual damascene processes. The illustrated structure includes further metallization levels with corresponding dielectric layers **165**, **166** and **167**, as well as an uppermost or top metallization layer **168**. The individual layers **165-168** in this example include conductive interconnect structures **162** and associated vias or contact plugs **163**.

[0027] The semiconductor structure, the electronic components (e.g., the transistors **101**), the capacitor **130**, the first dielectric structure layer **154** and the upper metallization structure **156** form a wafer or die **170** with an upper side or surface **171**. The upper side **171** of the metallization structure **156** forms an upper side of the wafer or die **170**. The top metallization layer **168** includes conductive features **169**, such as upper most aluminum vias. The conductive features **169** include a side or surface at the upper side **171** of the wafer or die **170** at the top of the uppermost metallization layer **168**. Any number of conductive features **169** may be provided. One or more of the conductive features **169** can be electrically coupled with an electronic component such as one of the transistors **101**.

[0028] The upper ILD dielectric layer **168** in one example is covered by one or more passivation layers **173** (e.g., protective overcoat (PO) and/or passivation layers), for example, silicon nitride (SiN), silicon oxynitride (SiO_xN_y), or silicon dioxide (SiO_2). In one example, the passivation layer or layers **173** include one or more openings that expose a portion of the conductive features **169** to allow electrical connection of the features **169** to corresponding contact structures **174**. The contact structures **174** extend outward (e.g., upward along the "Z" direction in FIG. 1) from the

upper side **171** of the metallization structure **156**. The individual contact structures **174** in one example include a conductive seed layer, such as copper that extends outward from the upper side **171** of the metallization structure **156**. In one example, the contact structure **174** includes titanium (Ti) or titanium tungsten (TiW).

[0029] The metallization structure **154**, **156** includes first conductive features **160**, **162** of the metallization structure **154**, **156** that connect the first polysilicon **126** to the first deep doped region **122**. This provides an isolation trench structure **120** that electrically isolates the active region **110** of the semiconductor structure from the capacitor **130** and from other regions of the wafer or die **170**. In addition, the metallization structure includes second conductive features **160**, **162** that are connected to the second polysilicon **136** to form a first capacitor plate, as well as further conductive features **160**, **162** that are connected to the second deep doped region **132** to form a second capacitor plate. The metallization structure **154**, **156** allows for further conductive connections (not shown) to connect the first and second capacitor plates to other circuitry within the wafer or die **170**, and/or to provide external connection for one or both of the first and second capacitor plates.

[0030] FIG. 2 shows a top view of a portion of the device **100**. In the illustrated example, the isolation structure **120** extends around the lateral periphery of the active region **110**, and also extends around three sides of a capacitor region. In this example, the capacitor region includes multiple capacitor trenches **131**, three of which are shown in the side view of FIG. 1. In one example, the capacitor trench width **138** is approximately $1.2\ \mu\text{m}$, and a spacing distance between adjacent capacitor structures is approximately $0.6\ \mu\text{m}$. In one example, a shallow n-well implant (e.g., regions **129** in FIG. 1, not shown in FIG. 2) extends into the capacitor region by approximately $0.1\ \mu\text{m}$, and encloses the capacitor region by approximately $0.65\ \mu\text{m}$. In one example, the NBL **104** extends into the capacitor region as shown in FIG. 1. In another example (not shown) the capacitor region is enclosed by the NBL **104**. In one example, a silicide block layer (not shown) extends beyond the capacitor region by approximately $0.25\ \mu\text{m}$, and extends into the capacitor region by approximately $0.255\ \mu\text{m}$.

[0031] Referring also to FIGS. 3-18, FIG. 3 shows a method **300** to fabricate an electronic device, such as an integrated circuit or standalone device. The illustrated method **300** also includes a process or method to fabricate an isolation structure in a semiconductor device. FIGS. 4-18 show integrated circuit of FIGS. 1 and 2 at various stages of fabrication according to the method **300**. The method **300** begins at **302** with an n-type implantation to form an n-doped region, such as the NBL region **104** in FIG. 1.

[0032] In one example, a first epitaxial silicon layer is formed over the upper surface of a silicon wafer substrate **102**, and all or a portion of the first epitaxial layer is implanted with n-type dopants (e.g., Sb, etc.) at **302** to form the NBL **104**. In one example, all or a portion of the first epitaxial layer is implanted at **303** with p-type dopants (e.g., boron, etc.) to form the p-type buried layer **106** with the upper side **107**. In one example, the PBL region **106** is formed using ion implantation through the final silicon surface (e.g., the top of the second epitaxial layer), with a depth set by using a high implantation energy. In one example, a further epitaxial silicon deposition process is performed at **304**, which deposits a second epitaxial silicon

layer over the first epitaxial layer. At **306**, the semiconductor surface layer **108** (e.g., labeled P-BODY) is implanted with p-type majority carrier dopants (e.g., boron) and extends downward along the Z direction from the first side **103** to the upper side **107** of the PBL **106**.

[**0033**] The method **300** also includes depositing an etch stop layer at **306**. FIG. 4 illustrates one example, in which a deposition process **402** is performed that deposits a nitride or oxynitride or oxide layer **400** on the first side **103** of the semiconductor structure. In one example, the layer **400** operates as an etch stop layer for subsequent planarization, such as chemical mechanical polishing (CMP). In one example, the etch stop layer **400** includes a pad oxide formed to a thickness of approximately 150 Å, such as 100-160 Å, and a nitride formed over the pad oxide to a thickness of approximately 0.2 μm.

[**0034**] The method **300** further includes depositing and patterning a thick resist layer at **308** with openings for isolation structures and second openings for trench capacitors. FIG. 5 shows one example, in which a process **503** is performed. The process **503** deposits and patterns a resist mask **500** over the hard mask layer **400** on the first surface **103** of the semiconductor structure. The process **503** in one example includes forming the resist layer **500** and patterning the first opening **501** with a first width **128**, as well as patterning the second opening **502** with a second width **138**, where the first width **128** is greater than the second width **138**. The first opening **501** is patterned above the prospective isolation structures **120** with a width **128** that corresponds to the desired width of the prospective isolation structure trenches **121** (e.g., FIG. 1). The second openings **502** are patterned above the prospective capacitor structure **130** with widths **138** that correspond to the desired widths of the prospective capacitor trenches **131** (FIG. 1). In one example, the width **128** of the first resist opening **501** is approximately 1.5 μm, and the width **138** of the second resist openings **502** is approximately 1.2 μm.

[**0035**] The method **300** continues at **310** with deep trench etching through the nitride **400** and silicon of the semiconductor surface layer **108**, the PBL **106**, and through at least a portion of the NBL **104** to form the trenches **121** and **131** using the patterned resist **500** as an etch mask. FIG. 6 shows one example, in which an etch process **600** etches through the resist opening **501** first trench **121** extending through the semiconductor surface layer **108** into the buried layer **104**. The etch process **600** concurrently etches through the second openings **502** to form the trenches **131** that extend into the NBL **104**. In the illustrated example, the first trench width **128** generally corresponds to the dimension of the first opening **501**, and the second trench width **138** generally corresponds to the dimension of the second opening **502**. The wider first opening **501** causes the first trench **121** to extend to the first depth **127** (e.g., approximately 6.8 μm, such as 6.2 μm to 7.2 μm, which is greater than the second depth **137** of the second trenches **131**).

[**0036**] Continuing at **312** and **314**, the method **300** further includes one or more deep trench implantations to form the first deep doped region **122** surrounding the first trench **121** and the second deep doped region **132** surrounding the second trench **131**. FIGS. 7 and 8 show an example that includes performing a first implantation process **700** using the remaining resist mask **500** to concurrently implant n-type dopants (e.g., phosphorus) through the openings **501** and **502** to form the first and second deep doped regions **122**

and **132**, respectively. The first deep doped region **122** surrounds the first trench **121** and extends from the semiconductor surface layer **108** to the buried layer **104**. The second deep doped region **132** surrounds the second trench **131** and extends from the semiconductor surface layer **108** to the buried layer **104**.

[**0037**] In one example, the first implantation process at **312** is an angled deep N trench sidewall implant. FIG. 7 shows an example, in which an angled implantation process **700** implants phosphorus or other n-type dopants through the resist openings **501** and **502** to implant the sidewalls of the trenches **121** and **131** at a dose of $9 \times 10^4 \text{ cm}^{-3}$ and an implantation energy of 200 keV to form the first and second deep doped regions **122** and **132** at an implant angle of 16 degrees, rotated four times with a 45 degree twist angle relative to a layout direction (e.g., relative to the direction of the transistor source, drain and gate fingers).

[**0038**] At **314**, a second implantation is performed to implant the bottoms of the regions **122** and **132**. FIG. 8 shows an example, in which an implantation process **800** is performed that implants phosphorus or other n-type dopants through the resist openings **501** and **502** to further implant the silicon below the bottoms of the trenches **121** and **131** at a dose of $9 \times 10^4 \text{ cm}^{-3}$ and an implantation energy of 50 keV at an implant angle of 0 degrees.

[**0039**] In one example, an anneal process is performed at **316** in FIG. 3, which oxidizes the silicon of the trench sidewalls and forms a dummy or sacrificial oxide layer on the sidewalls of the trenches **121** and **131**, for example, to a thickness of 150 Å. In one example, the sacrificial oxide is then stripped at **316** using a wet cleaning process with a 50% over etch to remove approximately 300 Å of material from the sidewalls of the trenches **121** and **131**. In one example, the over etch at **316** removes the deposited sacrificial oxide as well as original silicon that may have been damaged during the implantation at **312** and/or **314**.

[**0040**] The example method **300** continues at **318**, **320** and **322** with deposition processing to form dielectric liners of the sidewalls of the trenches **121** and **131**. The dielectric liner deposition processing deposits dielectric material through the first and second openings **501** and **502** of the remaining resist mask **500**. Any suitable dielectric can be used that forms a capacitor dielectric in the finished trench capacitor **130**. The dielectric liner can be a single layer or a multilayer structure. FIGS. 9-11 illustrate a multi-step deposition that forms an oxide-nitride-oxide (ONO) dielectric liner in each of the trenches **121** and **131**.

[**0041**] At **318** in FIG. 3, a first oxide deposition is performed, which forms first oxide layers on the sidewalls of the trenches **121** and **131**. FIG. 9 shows one example, in which an oxidation anneal process **900** is performed at 850 degrees C., that deposits silicon dioxide **123** (e.g., SiO_2) on the sidewall of the first trench **121**, and deposits silicon dioxide **133** and the sidewall of the second trenches **131**. In one example, the process **900** (850 degrees C.) causes thermal oxidation of the trench sidewall silicon to form the first oxide layers **123** and **133** to a thickness of approximately 65 Å, for example 60 Å to 70 Å.

[**0042**] At **320**, a second deposition process (e.g., a nitride deposition) is performed, that deposits a nitride layer on the first oxide layer along the sidewalls of the trenches **121** and **131**. FIG. 10 shows one example, in which a deposition process **1000** (e.g., deposition temperature of 650 degrees C.) deposits nitride material **124** (e.g., silicon nitride, silicon

oxynitride) through the first and second openings of the resist layer 500 onto the first oxide layer 123 in the first trench 121, and deposits nitride material 134 through the first and second openings of the resist layer 500 onto the first oxide layer 133 along the sidewalls in the second trenches 131. In one example, the process 1000 forms the nitride material layers 124 and 134 to a thickness of approximately 140 Å, for example, from 106 Å to 166 Å.

[0043] At 322, a third deposition process (e.g., an oxide deposition) is performed, that deposits a second oxide layer on the nitride layer along the sidewalls of the trenches 121 and 131. FIG. 11 shows one example, in which wet oxidation process 1100 grows a second oxide layer, such as an oxynitride 125 through the first opening on the nitride layer 124 in the first trench 121. The deposition process 1100 in this example deposits a second nitride layer 135 through the second openings of the resist layer 500 onto the nitride layer 134 in the second trenches 131. In one example, the process 1100 forms the second oxide material layers 125 and 135 to a thickness of approximately 20 Å, for example, 10 Å to 30 Å.

[0044] The example method 300 continues at 324 and 326, with deposition of polysilicon to fill the trenches 121 and 131. FIG. 12 shows one example, in which a first polysilicon deposition process 1200 (e.g., at 324 in FIG. 3) deposits a first polysilicon 126 through the first opening of the resist layer 500 to fill the first trench 121. The first polysilicon deposition process 1200 also deposits a second polysilicon 136 through the second openings of the resist layer 500 to fill the second trenches 131. The initial deposition process 1200 in one example deposits p-doped polysilicon 126, 136 with p-type majority carrier dopants (e.g., boron) to a thickness of 3400 Å.

[0045] At 326, a second polysilicon deposition is performed that deposits a polysilicon 126 to fill the trench 121, and polysilicon 136 to fill the second trenches 131. FIG. 13 shows one example, in which a second polysilicon deposition process 1300 deposits on doped polysilicon to fill the trenches 121 and 131, for example, to a thickness of approximately 10,000 Å. In one example, the target polysilicon deposition thickness is approximately 13,400 Å, such as 10,900 Å to 15,900 Å, in order to fill the trenches 121 and 131. As shown in FIGS. 12 and 13, in one example, the initial polysilicon deposition process 1200 and the trench fill deposition process 1300 form polysilicon 126, 136 on both sides of the device 100, including deposition along the bottom side 105 of the semiconductor structure.

[0046] Continuing at 328-332 in FIG. 3, the method 300 further includes a back side polysilicon removal or stripping step at 328. In one example, wet etch process (not shown) is performed, that strips the excess polysilicon from the bottom side 105 of the semiconductor structure. At 330, the top side of the wafer is planarized. FIG. 14 shows one example, in which a chemical mechanical polishing (CMP) process 1400 removes the polysilicon remaining above the top side 103 of the wafer, and planarizes the top side of the wafer. The CMP process 1500 stops on the nitride hard mask layer 400 as shown in FIG. 14. At 332, a wet etch process is performed to strip the remaining nitride hard mask layer. FIG. 15 shows one example, in which a wet etch process 1500 is performed, that removes the remaining nitride layer from the top side 103 of the wafer.

[0047] The method 300 also includes shallow trench isolation (STI) processing at 334. FIG. 16 shows one example,

in which an STI fabrication process 1600 is performed that etches trenches and fills the trenches with an oxide material 118. In one example, the STI processing includes growing a pad oxide, depositing a nitride layer (not shown) using low-pressure chemical vapor deposition (LPCVD), patterning and etching trenches in the silicon of the surface layer 108 and in the liner and silicon of the trenches 121 and 131, growing a liner oxide in the STI trenches to repair silicon and round off sharp corners, followed by plasma enhanced CVD (PECVD) deposition of TEOS oxide. The processing further includes another chemical mechanical polishing of the trench oxide using the nitride as an etch stop, followed by removal of the nitride etch stop layer.

[0048] At 336, transistor fabrication processing is performed, including fabricating the transistors 101. FIG. 17 shows a simplified example, in which the transistor fabrication processing 1700 is performed to create the transistor structures 101. In one example, the transistor fabrication at 336 includes performing an implantation process that implants n-type majority carrier into the semiconductor surface layer 108 to form the shallow implant region 129 extending along a side of the first trench 121 within the deep doped region 122. In one example, the same implantation process is used to form lowercase N-p-type source/drain regions of the transistors 101 or features of other components (not shown) of the wafer 170.

[0049] At 338 in FIG. 3, the method 300 continues with metallization to form one or more layers of dielectric with conductive metal features to provide interconnection for the transistors and/or other components of the wafer 170. The metallization processing at 338 includes forming a conductive features to provide capacitor plates for the trench capacitors 130, and to interconnect features of the trench-based isolation structures 120. FIG. 18 illustrates a portion of the metallization processing 1800, that forms first conductive features 160, 162 that extend over the semiconductor surface layer 108 and that connect the first polysilicon 126 to the first deep doped region 122 to form the trench-based isolation structure 120. The metallization processing 1800 also forms second conductive features 160, 162 that connect to the second polysilicon 136 to form a first capacitor plate, and additionally forms further conductive features 160, 162 of the metallization structure 154, 156 that connect to the second deep doped region 132 to form a second capacitor plate.

[0050] The process 300 in FIG. 3 also includes die singulation at 340 to separate one or more product dies from the wafer 170. The processing at 340 also includes packaging to provide one or more finished semiconductor devices, such as stand-alone components and/or integrated circuits.

[0051] The method 300 provides an integrated process for concurrent fabrication of both trench isolation structures 120 and high density trench capacitors 130 using a shared resist mask 500. Example implementations also use a thick resist mask 500 to facilitate processing of both trench types. The use of a thick shared mask and similar trench structure architectures for both isolation structures 120 and trench capacitors 130 provides economy of processing steps and costs. In addition, the disclosed examples facilitate density advantages compared with use of non-trench isolation structures with deep well implants. In this regard, deep implant isolation features that extend into a semiconductor structure to a buried layer (e.g., a deep n-well implanted and diffused to extend into the NBL 104) involve significant lateral

diffusion, thereby extending the lateral extent of the isolation features. Disclosed examples remove the need for a separate deep implant mask, and also facilitate reduction in the deep doped region resistance by using a trench pillar type isolation layout. The disclosed examples, in contrast, provide lateral area control for the isolation features **120** for reduced isolation to isolation spacing using self-aligned deep doped region implantation on deep trench sidewalls, in addition to the fabrication cost and time advantages of concurrently constructing the isolation structures **120** and the trench capacitors **130**. These features provide significant advantages, particularly in combination with simple modification of metallization structures by shorting bottom plate and top plate of (e.g., the deep doped region **122** and the p-type polysilicon structure **126**) to form the isolation structures **120**. Modifications are possible in the described embodiments, and other embodiments are possible, within the scope of the claims.

The following is claimed:

1. A semiconductor device, comprising:
 - a semiconductor structure, including:
 - a semiconductor surface layer including majority carrier dopants of a first conductivity type, and
 - a buried layer including majority carrier dopants of a second conductivity type;
 - a metallization structure extending over the semiconductor surface layer; and
 - an isolation structure, including:
 - a first trench extending through the semiconductor structure to the buried layer,
 - a first dielectric liner extending along a sidewall of the first trench from the semiconductor surface layer to the buried layer,
 - a first polysilicon including majority carrier dopants of the first conductivity type, the first polysilicon extending inside the first dielectric liner and filling the first trench to a top side of the semiconductor surface layer,
 - a first deep doped region including majority carrier dopants of the second conductivity type, the first deep doped region surrounding the first trench and extending from the semiconductor surface layer to the buried layer, and
 - first conductive features of the metallization structure that connect the first polysilicon to the first deep doped region.
2. The semiconductor device of claim **1**, further comprising a capacitor, the capacitor including:
 - a second trench extending through the semiconductor structure to the buried layer,
 - a second dielectric liner extending along a sidewall of the second trench from the semiconductor surface layer to the buried layer,
 - a second polysilicon including majority carrier dopants of the first conductivity type, the second polysilicon extending inside the second dielectric liner and filling the second trench to a top side of the semiconductor surface layer,
 - a second deep doped region including majority carrier dopants of the second conductivity type, the second deep doped region surrounding the second trench and extending from the semiconductor surface layer to the buried layer,

second conductive features of the metallization structure connected to the second polysilicon to form a first capacitor plate, and

further conductive features of the metallization structure connected to the second deep doped region to form a second capacitor plate.

3. The semiconductor device of claim **2**, wherein the first trench has a first depth, wherein the second trench has a second depth, and wherein the first depth is greater than the second depth.

4. The semiconductor device of claim **3**, wherein the first trench has a first width, wherein the second trench has a second width, and wherein the first width is greater than the second width.

5. The semiconductor device of claim **2**, wherein the first trench has a first width, wherein the second trench has a second width, and wherein the first width is greater than the second width.

6. The semiconductor device of claim **2**,

wherein the first dielectric liner includes:

- a first oxide layer extending along the sidewall of the first trench from the semiconductor surface layer to the buried layer,

- a nitride layer extending along the first oxide layer from the semiconductor surface layer to the buried layer, and

- a second oxide layer extending along the nitride layer from the semiconductor surface layer to the buried layer; and

wherein the second dielectric liner includes:

- a third oxide layer extending along the sidewall of the second trench from the semiconductor surface layer to the buried layer,

- a second nitride layer extending along the third oxide layer from the semiconductor surface layer to the buried layer, and

- a fourth oxide layer extending along the second nitride layer from the semiconductor surface layer to the buried layer.

7. The semiconductor device of claim **2**, wherein the capacitor comprises:

- a plurality of second trenches extending through the semiconductor structure to the buried layer, each of the second trenches surrounded by the second deep doped region and including: a corresponding second dielectric liner extending along a sidewall of the second trench from the semiconductor surface layer to the buried layer, and

a corresponding second polysilicon including majority carrier dopants of the first conductivity type, the second polysilicon extending inside the second dielectric liner and filling the second trench to the top side of the semiconductor surface layer.

8. The semiconductor device of claim **7**, wherein the capacitor further comprises a shallow implant region having majority carrier dopants of the second conductivity type and extending in the semiconductor surface layer between the plurality of second trenches within the second deep doped region.

9. The semiconductor device of claim **1**, wherein the first dielectric liner includes:

- a first oxide layer extending along the sidewall of the first trench from the semiconductor surface layer to the buried layer;

a nitride layer extending along the first oxide layer from the semiconductor surface layer to the buried layer; and a second oxide layer extending along the nitride layer from the semiconductor surface layer to the buried layer.

10. The semiconductor device of claim **1**, further comprising a shallow implant region having majority carrier dopants of the second conductivity type and extending in the semiconductor surface layer along a side of the first trench within the first deep doped region.

11. A semiconductor device, comprising:

- a semiconductor surface layer with majority carrier dopants of a first conductivity type;
- a buried layer with majority carrier dopants of a second conductivity type;
- a first trench extending through the semiconductor surface layer to the buried layer;
- a second trench extending through the semiconductor surface layer to the buried layer;
- a first deep doped region surrounding the first trench and extending from the semiconductor surface layer to the buried layer;
- a second deep doped region surrounding the second trench and extending from the semiconductor surface layer to the buried layer;
- a first dielectric liner on a sidewall of the first trench and a second dielectric liner on a sidewall of the second trench;
- a first polysilicon in the first trench and a second polysilicon in the second trench;
- first conductive features of a metallization structure extending over the semiconductor surface layer that connect the first polysilicon to the first deep doped region to form an isolation structure;
- second conductive features of the metallization structure that connect to the second polysilicon to form a first capacitor plate; and
- further conductive features of the metallization structure that connect to the second deep doped region to form a second capacitor plate.

12. The semiconductor device of claim **11**, wherein the first and second dielectric liners comprise:

- a first oxide layer;
- a nitride layer on the first oxide layer; and
- a second oxide layer on the nitride layer.

13. The semiconductor device of claim **11**, wherein the first trench has a first depth, wherein the second trench has a second depth, and wherein the first depth is greater than the second depth.

14. The semiconductor device of claim **11**, further comprising a shallow implant region extending along a side of the first trench within the first deep doped region.

15. The semiconductor device of claim **11**, wherein the first trench has a first width, wherein the second trench has a second width, and wherein the first width is greater than the second width.

16. A semiconductor device, comprising:

- a semiconductor structure, including:
 - a semiconductor surface layer of a first conductivity type, and
 - a buried layer a second conductivity type;
- a metallization structure extending over the semiconductor surface layer;
- an isolation structure, including:
 - a first trench extending through the semiconductor structure to the buried layer,
 - a first dielectric liner extending along a sidewall of the first trench from the semiconductor surface layer to the buried layer,
 - a first polysilicon of the first conductivity type, the first polysilicon extending inside the first dielectric liner and filling the first trench to a top side of the semiconductor surface layer,
 - a first deep doped region of the second conductivity type, the first deep doped region surrounding the first trench and extending from the semiconductor surface layer to the buried layer, and
 - first conductive features of the metallization structure that connect the first polysilicon to the first deep doped region; and
- a capacitor, including:
 - a second trench extending through the semiconductor structure to the buried layer,
 - a second dielectric liner extending along a sidewall of the second trench from the semiconductor surface layer to the buried layer,
 - a second polysilicon of the first conductivity type, the second polysilicon extending inside the second dielectric liner and filling the second trench to a top side of the semiconductor surface layer,
 - a second deep doped region of the second conductivity type, the second deep doped region surrounding the second trench and extending from the semiconductor surface layer to the buried layer,
 - second conductive features of the metallization structure connected to the second polysilicon to form a first capacitor plate, and
 - further conductive features of the metallization structure connected to the second deep doped region to form a second capacitor plate.

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